

2SB1462J

Silicon PNP epitaxial planar type

For general amplification

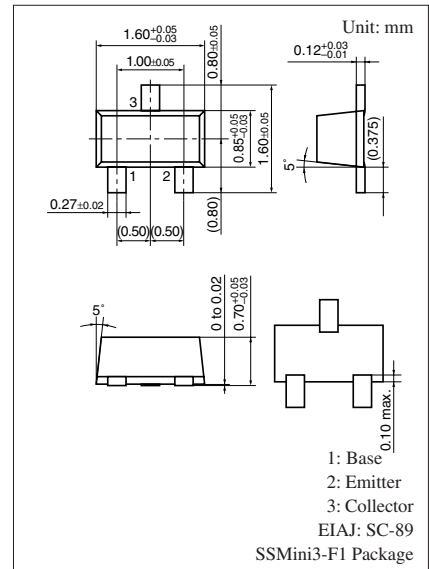
Complementary to 2SD2216J

■ Features

- High forward current transfer ratio h_{FE}
- SS-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	-60	V
Collector-emitter voltage (Base open)	V_{CEO}	-50	V
Emitter-base voltage (Collector open)	V_{EBO}	-7	V
Collector current	I_C	-100	mA
Peak collector current	I_{CP}	-200	mA
Collector power dissipation	P_C	125	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

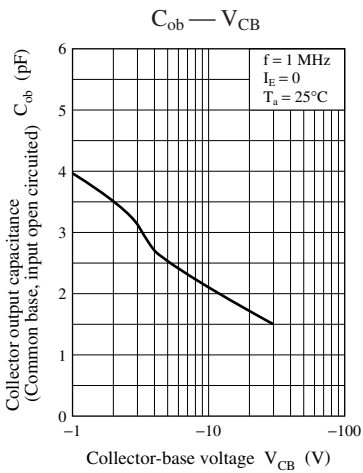
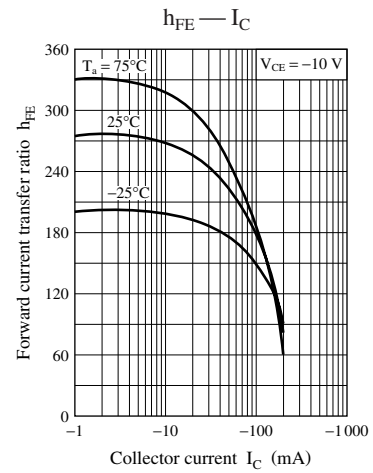
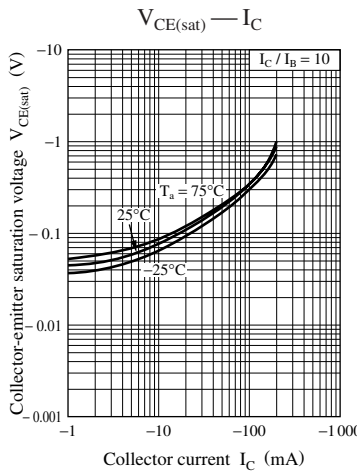
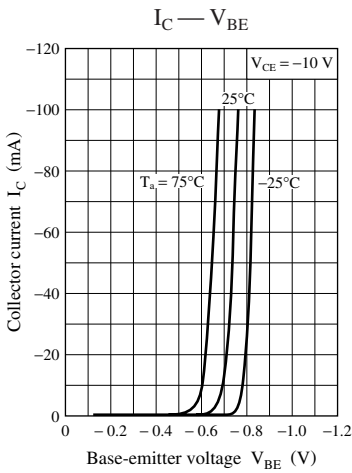
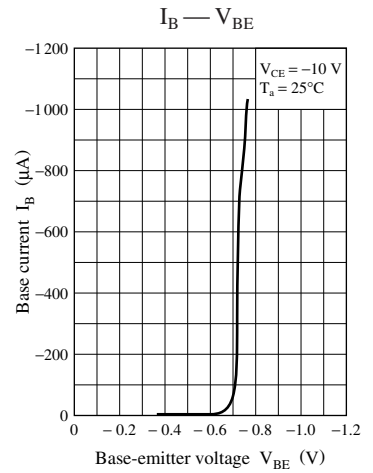
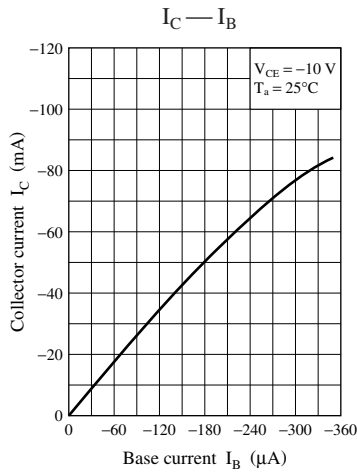
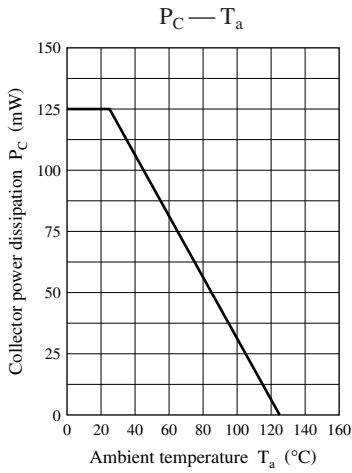


Marking Symbol: A

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = -10 \mu\text{A}, I_E = 0$	-60			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = -100 \mu\text{A}, I_B = 0$	-50			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = -10 \mu\text{A}, I_C = 0$	-7			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -20 \text{V}, I_E = 0$			-0.1	μA
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = -10 \text{V}, I_E = 0$			-100	μA
Forward current transfer ratio	h_{FE}	$V_{CE} = -10 \text{V}, I_C = -2 \text{mA}$	180		390	—
Collector-emitter saturation voltage *1	$V_{CE(sat)}$	$I_C = -100 \text{mA}, I_B = -10 \text{mA}$		-0.3	-0.5	V
Transition frequency	f_T	$V_{CB} = -10 \text{V}, I_E = 1 \text{mA}, f = 200 \text{MHz}$		80		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{CB} = -10 \text{V}, I_E = 0, f = 1 \text{MHz}$		2.7		pF

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.



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